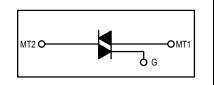
Triacs Silicon Bidirectional Triode Thyristors

... designed primarily for full-wave ac control applications, such as lighting systems, heater controls, motor controls and power supplies; or wherever full-wave silicon-gate-controlled devices are needed.

- Off-State Voltages to 800 Volts
- All Diffused and Glass Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Thermal Resistance and High Heat
 Dissipation
- Gate Triggering Guaranteed in Three Modes (MAC223FP Series) or Four Modes (MAC223AFP Series)



Series

25 AMPERES RMS

200 thru 800 VOLTS

MAC223FP Series

MAC223AFP

CASE 221C-02 STYLE 3

MAXIMUM RATINGS (T_J = 25° unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ (T _J = -40 to +125°C, 1/2 Sine Wave 50 to 60 Hz, Gate Open) MAC223-4FP, MAC223A4FP	VDRM	200	Volts
MAC223-6FP, MAC223A6FP MAC223-8FP, MAC223A8FP MAC223-10FP, MAC223A10FP		400 600 800	
On-State RMS Current (T _C = +80°C) Full Cycle Sine Wave 50 to 60 Hz ⁽²⁾	I _{T(RMS)}	25	Amps
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, $T_C = 80^{\circ}C$, preceded and followed by rated current)	ITSM	250	Amps
Circuit Fusing (t = 8.3 ms)	l ² t	260	A ² s
Peak Gate Power (t $\leq 2 \mu$ s)	PGM	20	Watts
Average Gate Power (T _C = +80°C, t \leq 8.3 ms)	PG(AV)	0.5	Watt
Peak Gate Current (t $\leq 2 \mu s$)	I _{GM}	2	Amps
Peak Gate Voltage (t \leq 2 µs)	V _{GM}	±10	Volts
RMS Isolation Voltage (T _A = 25°C, Relative Humidity \leq 20%)	V(ISO)	1500	Volts
Operating Junction Temperature	ТJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Mounting Torque		8	in. lb.

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1.2	°C/W
Thermal Resistance, Case to Sink	R ₀ CS	2.2	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	60	°C/W



MAC223FP Series MAC223AFP Series

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current(1) $T_J = 25^{\circ}C$ $(V_D = Rated V_{DRM}, Gate Open)$ $T_J = 125^{\circ}C$	IDRM			10 2	μA mA
Peak On-State Voltage (I_{TM} = 35 A Peak, Pulse Width \leq 2 ms, Duty Cycle \leq 2%)	VTM	—	1.4	1.85	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY	IGT		20 30	50 75	mA
	VGT	 0.2 0.2	1.1 1.3 0.4 0.4	2 2.5 —	Volts
Holding Current (V _D = 12 V, I _{TM} = 200 mA, Gate Open)	Ч	—	10	50	mA
Gate Controlled Turn-On Time (V_D = Rated V_{DRM} , I _{TM} = 35 A Peak, I _G = 200 mA)	tgt	—	1.5	—	μs
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM} , Exponential Waveform, T_C = 125°C)	dv/dt	—	40	—	V/µs
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 35 A Peak, Commutating di/dt = 12.6 A/ms, Gate Unenergized, T_C = 80°C)	dv/dt(c)	-	5	_	V/µs

1. Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.

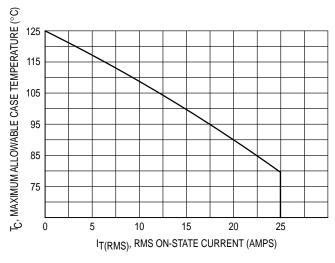


Figure 1. RMS Current Derating

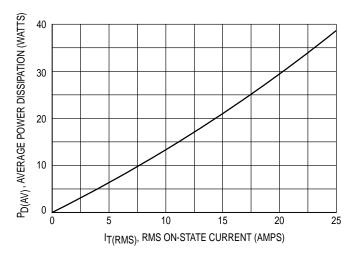
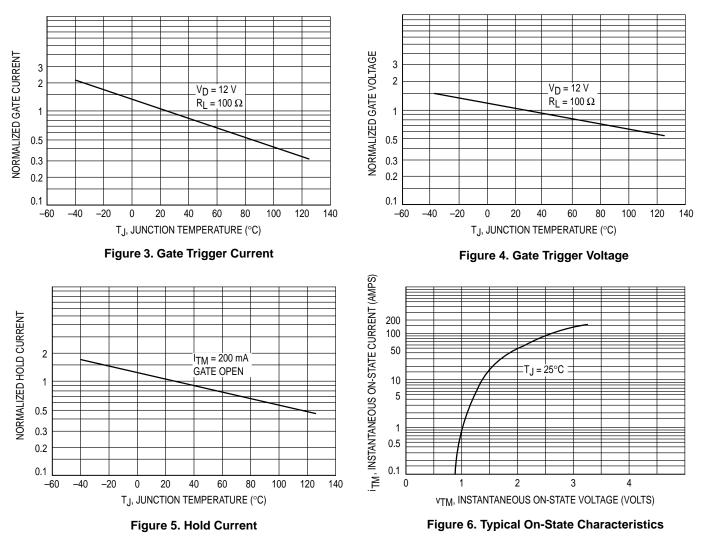


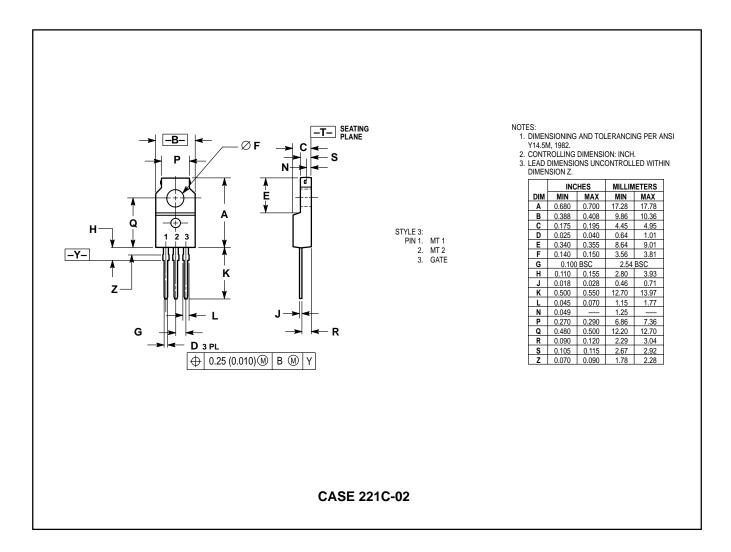
Figure 2. On-State Power Dissipation

MAC223FP Series MAC223AFP Series



TYPICAL CHARACTERISTICS

PACKAGE DIMENSIONS



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